### 1.6 MHz Boost Converter With 30V Internal FET Switch

## General Description

The AME5140 switching regulator is current-mode boost converters operating at fixed frequency of 1.6 MHz .

The use of SOT-25/TSOT-25, DFN-8(3mmx3mmx 0.75 mm ) \& MSOP- 8 packages, made possible by the minimal power loss of the internal 1.8A switch, and use of small inductor and capacitors result in the industry's highest power density. The 30V internal switch makes these solutions perfect for boosting to voltages up to 30 V .

These parts have a logic-level shutdown pin that can be used to reduce quiescent current and extend battery life. Protection is provided through cycle-by-cycle current limiting and thermal shutdown. Internal compensation simplifies and reduces component count.

## Features

- 30V DMOS FET Switch
- 1.6 MHz Switching Frequency
- Low $\mathrm{R}_{\text {Dson }}$ DMOS FET
- Switch Current Up to 1.8A
- Wide Input Voltage Range (2.7V-5.5V)
- Low Shutdown Current ( $<1 \mu \mathrm{~A}$ )
- SOT-25/TSOT-25, DFN-8(3mmx3mmx0.75mm) \& MSOP-8 Packages
- Uses Tiny Capacitors and Inductor
- Cycle-by-Cycle Current Limiting
- All AME's Lead Free Products Meet RoHS Standards


## Applications

- White LED Current Source
- PDA's and Palm-Top Computers
- Digital Cameras
- Portable Phones and Games
- Local Boost Regulator


## Typical Application



Figure 1. 4.2V to 5V Boost Converter


Figure 2. 5V to 12V Boost Converter


Figure 3.5 V to 18 V Boost Converter

## Function Block Diagram



Figure 4. Functional Block Diagram

# 1.6 MHz Boost Converter With 30V Internal FET Switch 

## Pin Configuration



* Die Attach:

Conductive Epoxy

AME5140BEQA

1. IN
2. EN
3. GND
4. FB
5. SW
6. SW
7. GND
8. GND

* Die Attach:

Conductive Epoxy

DFN-8
(3mmx3mmx0.75mm)
Top View


## AME5140AEVA

1. NC
2. FB
3. NC
4. SW
5. NC
6. IN
7. EN
8. NC

## * Die Attach: Conductive Epoxy

Note: The trapezoid area enclosed by dashed line represents Exposed Pad and is GND.

## AME5140

### 1.6 MHz Boost Converter with 30V Internal FET Switch

## ■ Pin Description (Continued)

## AME5140AEEV SOT-25/TSOT-25

| Pin Number | Pin Name | Pin Description |
| :---: | :---: | :--- |
| 1 | SW | Power Switch input. <br> This is the drain of the internal NMOS power switch. <br> Minimize the metal trace area connected to this pin to minimize EMI. |
| 2 | GND | Ground. Tie directly to ground plane. |
| 3 | FB | Output voltage feedback input. <br> Set the output voltage by selecting values for R1 and R2 using: <br> EN $2\left(\frac{V_{\text {out }}}{1.23 V}-1\right)$ |
| 4 | En | Enable, active high. <br> The enable pin is an active high control. Tie this pin above 2V to enable the <br> device. Tie this pin below 0.4V to turn off the device. |
| 5 | $\mathbb{I N}$ | Analog and Power input. Input Supply Pin. <br> Place bypass capacitor as close to VIN as possible. |

## AME5140BEQA MSOP-8

| Pin Number | Pin Name | Pin Description |
| :---: | :---: | :---: |
| 1 | IN | Analog and Power input. Input Supply Pin. <br> Place bypass capacitor as close to $\mathrm{V}_{\mathrm{IN}}$ as possible. |
| 2 | EN | Enable, active high. <br> The enable pin is an active high control. Tie this pin above 2 V to enable the device. Tie this pin below 0.4 V to turn off the device. |
| 3 | GND | Ground. Tie directly to ground plane. |
| 4 | FB | Output voltage feedback input. <br> Set the output voltage by selecting values for R1 and R2 using: $R 1=R 2\left(\frac{V_{\text {out }}}{1.23 V}-1\right)$ <br> Connect the ground of the feedback network to a GND plane. |
| 5 | SW | Power Switch input. <br> This is the drain of the internal NMOS power switch. <br> Minimize the metal trace area connected to this pin to minimize EMI. |
| 6 | SW | Power Switch input. <br> This is the drain of the internal NMOS power switch. <br> Minimize the metal trace area connected to this pin to minimize EMI. |
| 7 | GND | Ground. Tie directly to ground plane. |
| 8 | GND | Ground. Tie directly to ground plane. |

### 1.6 MHz Boost Converter With 30V Internal FET Switch

■ Pin Description
AME5140AEVA DFN-8(3mmx3mmx0.75mm)

| Pin Number | Pin Name | Pin Description |
| :---: | :---: | :--- |
| 1 | NC | Not Connected |
| 2 | FB | Output voltage feedback input. <br> Set the output voltage by selecting values for R1 and R2 using: <br> $R 1=R 2\left(\frac{V_{\text {out }}}{1.23 V}-1\right)$ <br> Connect the ground of the feedback network to a GND plane. |
| 3 | NC | Not Connected |
| 4 | NC | Power Switch input. <br> This is the drain of the internal NMOS power switch. <br> Minimize the metal trace area connected to this pin to minimize EMI. |
| 5 | IN | Not Connected |
| 7 | Analog and Power input. Input Supply Pin. |  |
| Place bypass capacitor as close to VIN as possible. |  |  |

### 1.6 MHz Boost Converter with 30V Internal FET Switch

- Ordering Information


| Pin <br> Configuration | Operating Ambient Temperature Range | Package Type | Number of Pins | Output Voltage | Special Feature1 | Special Feature2 <br> (For DFN package only) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| A 1. SW <br> (SOT-25) 2. GND <br> (TSoT-25) 3. FB <br>  4. EN <br>  5. IN | E: $-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$ | E: SOT-2X <br> V: DFN <br> Q: MSOP | $\begin{aligned} & \text { V: } 5 \\ & \text { A: } 8 \end{aligned}$ | ADJ: Adjustable |  <br> Y: Low profile (For TSOT-25 only) <br> Z: Lead free | 3: $3 \times 3 \times 0.75(\mathrm{~mm})(\mathrm{LxW} \times \mathrm{H})$ |
| A 1. NC <br> (DFN-8) 2. FB <br>  3. NC <br>  4. SW <br>  5. NC <br>  6. IN <br>  7. EN <br>  8. NC |  |  |  |  |  |  |
| B 1. IN <br> (MSOP-8) 2. EN <br>  3. GND <br>  4. FB <br>  5. SW <br>  6. SW <br> 7. GND  <br> 8. GND  |  |  |  |  |  |  |

AME5140

### 1.6 MHz Boost Converter With 30V Internal FET Switch

■ Ordering Information

| Part Number | Marking | Output <br> Voltage | Package | Operating Ambient <br> Temperature Range |
| :---: | :---: | :---: | :---: | :---: |
| AME5140AEEVADJZ | BDRww | ADJ | SOT-25 | $-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$ |
| AME5140AEEVADJY | BDRww | ADJ | TSOT-25 | $-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$ |
| AME5140AEVAADJZ-3 | BFK <br> yyww | ADJ | DFN-8 <br> $(3 \mathrm{~mm} 3 \mathrm{mmx0.75m})$ | $-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$ |
| AME5140BEQAADJZ | 5140 <br> Cyww | ADJ | MSOP-8 | $-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$ |

[^0]
### 1.6 MHz Boost Converter with

## - Absolute Maximum Ratings

| Parameter | Symbol | Maximum | Unit |
| :--- | :---: | :---: | :---: |
| Input Supply Voltage | $\mathrm{V}_{\mathrm{IN}}$ | 6 | V |
| EN, FB Voltages | $\mathrm{V}_{\mathrm{EN}}, \mathrm{V}_{\mathrm{FB}}$ | $\mathrm{V}_{\mathrm{IN}}$ | V |
| SW Voltage | $\mathrm{V}_{\mathrm{SW}}$ | 30 | V |
| ESD Classification | $\mathrm{B}^{*}$ |  |  |

Caution: Stress above the listed absolute maximum rating may cause permanent damage to the device.

* HBM B:2000V~3999V
- Recommended Operating Conditions

| Parameter | Symbol | Rating | Unit |
| :---: | :---: | :---: | :---: |
| Ambient Temperature Range | $\mathrm{T}_{\mathrm{A}}$ | -40 to 85 | ${ }^{\circ} \mathrm{C}$ |
| Junction Temperature Range | $\mathrm{T}_{\mathrm{J}}$ | -40 to 125 |  |
| Storage Temperature Range | $\mathrm{T}_{\text {STG }}$ | -65 to 150 |  |

■ Thermal Information

| Parameter | Package | Die Attach | Symbol | Maximum | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Thermal Resistance* (Junction to Case) | SOT-25 / TSOT-25 | Conductive Epoxy | $\theta_{\text {Jc }}$ | 81 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  | MSOP-8 |  |  | 100 |  |
|  | DFN-8 $(3 \mathrm{~mm} \times 3 \mathrm{~mm} \times 0.75 \mathrm{~mm})$ |  |  | 17 |  |
| Thermal Resistance (Junction to Ambient) | SOT-25 / TSOT-25 |  | $\theta_{\mathrm{JA}}$ | 260 |  |
|  | MSOP-8 |  |  | 206 |  |
|  | $\begin{array}{\|c\|} \hline \text { DFN-8 } \\ (3 \mathrm{~mm} 3 \mathrm{~mm} \times 0.75 \mathrm{~mm}) \end{array}$ |  |  | 125 |  |
| Internal Power Dissipation | SOT-25 / TSOT-25 |  | $P_{\text {D }}$ | 400 | mW |
|  | MSOP-8 |  |  | 625 |  |
|  | DFN-8 <br> $(3 \mathrm{~mm} \times 3 \mathrm{~mm} \times 0.75 \mathrm{~mm})$ |  |  | 800 |  |
| Maximum Junction Temperature |  |  |  | 150 | ${ }^{\circ} \mathrm{C}$ |
| Solder Iron (10 Sec)** |  |  |  | 350 |  |

[^1]AME5140

### 1.6 MHz Boost Converter With 30V Internal FET Switch

## Electrical Specifications

$V_{I N}=5 \mathrm{~V}, E N=V_{I N}, T_{A}=25^{\circ} \mathrm{C}, I_{L}=0 \mathrm{~A}$, unless otherwise noted.

| Parameter | Symbol | Test Condition |  | Min | Typ | Max | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Input Voltage | $\mathrm{V}_{\text {IN }}$ |  |  | 2.7 |  | 5.5 | V |
| Switch Current Limit | $\mathrm{I}_{\mathrm{CL}}$ | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  | 1.5 | 1.8 |  | A |
|  |  | $\mathrm{T}_{\mathrm{A}}=-40$ to $85^{\circ} \mathrm{C}$ |  | 1.2 |  |  |  |
| Switch ON Resistance | $\mathrm{R}_{\text {DSON }}$ |  | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  | 0.4 | 0.6 | $\Omega$ |
|  |  | $\mathrm{V}_{\mathrm{IN}}=5 \mathrm{~V}$ | $\mathrm{T}_{\mathrm{A}}=-40$ to $85^{\circ} \mathrm{C}$ |  |  | 0.7 |  |
|  |  | $\mathrm{V}_{\text {IN }}=3.3 \mathrm{~V}$ | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  | 0.5 | 0.7 |  |
|  |  |  | $\mathrm{T}_{\mathrm{A}}=-40$ to $85^{\circ} \mathrm{C}$ |  |  | 0.8 |  |
| EN Pin Bias Current | $\mathrm{I}_{\mathrm{EN}}$ | $\mathrm{EN}=0 \mathrm{~V}$ |  |  | 0 |  | $\mu \mathrm{A}$ |
|  |  | $\mathrm{EN}=5 \mathrm{~V}$ |  |  | 0 | 2 |  |
| Feedback Pin Reference Voltage | $V_{\text {FB }}$ | $\mathrm{V}_{\mathrm{IN}}=3 \mathrm{~V}$ |  | 1.205 | 1.23 | 1.255 | V |
| Feedback Pin Bias Current | $\mathrm{I}_{\text {FB }}$ | $\mathrm{V}_{\mathrm{FB}}=1.23 \mathrm{~V}$ |  |  | 60 | 500 | nA |
| Quiescent Current | $\mathrm{l}_{\mathrm{Q}}$ | $\mathrm{FB}=1.15 \mathrm{~V}$ (Switching) | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  | 2 |  | mA |
|  |  |  | $\begin{gathered} \mathrm{V}_{\mathrm{IN}}=5 \mathrm{~V} \\ \mathrm{~T}_{\mathrm{A}}=-40 \text { to } 85^{\circ} \mathrm{C} \end{gathered}$ |  |  | 3 |  |
|  |  | $\mathrm{FB}=1.3 \mathrm{~V}$ <br> (Not Switching) | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  | 400 |  | $\mu \mathrm{A}$ |
|  |  |  | $\begin{gathered} \mathrm{V}_{\mathrm{IN}}=5 \mathrm{~V} \\ \mathrm{~T}_{\mathrm{A}}=-40 \text { to } 85^{\circ} \mathrm{C} \end{gathered}$ |  |  | 500 |  |
| Shutdown Current |  | $\mathrm{EN}=0 \mathrm{~V}$ |  |  | 0.01 | 1 | $\mu \mathrm{A}$ |
| Undervoltage Lockout | UVP | Rising Edge |  | 2.15 | 2.35 | 2.55 | V |
| Over Temperature Protection | OTP | $\mathrm{V}_{\text {IN }}=2.7 \mathrm{~V}$ to 5.5 V |  |  | 160 |  | ${ }^{\circ} \mathrm{C}$ |
| OTP Hysteresis Temperature |  |  |  |  | 20 |  | ${ }^{\circ} \mathrm{C}$ |
| FB Voltage Line Regulation | $\frac{\Delta \mathrm{V}_{\text {FB }}}{\Delta \mathrm{V}_{\mathrm{IN}}}$ | $2.7 \mathrm{~V}<=\mathrm{V}_{\text {IN }}<=5.5 \mathrm{~V}$ |  |  | 0.02 |  | \%V |
| Switching Frequency | $\mathrm{f}_{\mathrm{sw}}$ | $\mathrm{V}_{\text {IN }}=3 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=-40$ to $85^{\circ} \mathrm{C}$ |  | 1 | 1.6 | 1.85 | MHz |
| Maximum Duty Cycle | $\mathrm{D}_{\text {MAX }}$ | $\mathrm{V}_{\text {IN }}=3 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=-40$ to $85^{\circ} \mathrm{C}$ |  | 86 | 93 |  | \% |
| Switch Leakage | Isw | $\mathrm{EN}=0 \mathrm{~V}$ |  |  | 0.1 | 2 | $\mu \mathrm{A}$ |
| EN Input Threshold (Low) (Shutdown) | EN <br> Threshold | $\mathrm{T}_{\mathrm{A}}=-40$ to $85^{\circ} \mathrm{C}$ |  |  |  | 0.4 | V |
| EN Input Threshold (High) (Enable the device) |  | $\mathrm{T}_{\mathrm{A}}=-40$ to $85^{\circ} \mathrm{C}$ |  | 2 |  |  |  |

## AME5140

### 1.6 MHz Boost Converter with 30V Internal FET Switch

## ■ Detailed Description

The AME5140 is a switching converter IC that operates at a fixed frequency $(1.6 \mathrm{MHz})$ for fast transient response over a wide input voltage range and incorporates pulse-bypulse current limiting protection. Operation can be best understood by referring to Figure 4. Because this is current mode control, a $33 \mathrm{~m} \Omega$ sense resistor in series with the switch FET is used to provide a voltage (which is proportional to the FET current) to both the input of the pulse width modulation (PWM) comparator and the current limit amplifier.

At the beginning of each cycle, the S-R latch turns on the FET. As the current through the FET increases, a voltage (proportional to this current) is summed with the ramp coming from the ramp generator and then fed into the input of the PWM comparator. When this voltage exceeds the voltage on the other input (coming from the Gm amplifier), the latch resets and turns the FET off. Since the signal coming from the Gm amplifier is derived from the feedback (which samples the voltage at the output), the action of the PWM comparator constantly sets the correct peak current through the FET to keep the output voltage in regulation.

Q1 and Q2 align with R3 - R6 form a bandgap voltage reference used by the IC to hold the output in regulation. The currents flowing through Q1 and Q2 will be equal, and the feedback loop will adjust the regulated output to maintain this. Because of this, the regulated output is always maintained at a voltage level equal to the voltage at the FB node "multiplied up" by the ratio of the output resistive divider.

The current limit comparator feeds directly into the flipflop that drives the switch FET. If the FET current reaches the limit threshold, the FET is turned off and the cycle terminated until the next clock pulse. The current limit input terminates the pulse regardless of the status of the output of the PWM comparator.

## - Application Hints

## Selecting The External Capacitors

The best capacitors for use with the AME5140 are multilayer Ceramic capacitors. They have the lowest ESR (equivalent series resistance) and highest resonance frequency, which makes them optimum for use with high frequency switching Converters. When selecting a ceramic capacitor, only X5R and X7R dielectric types should be used. Other types such as Z5U and Y5F have such severe loss of capacitance due to effects of temperature variation and applied voltage, they may provide as little as $20 \%$ of rated capacitance in many typical applications. Always consult capacitor manufacturer's data curves before selecting a capacitor. High-quality ceramic capacitors can be obtained from Taiyo-Yuden, AVX, and Murata.

## Selecting The Output Capacitor

A single ceramic capacitor of value $4.7 \mu \mathrm{~F}$ to $10 \mu \mathrm{~F}$ will provide sufficient output capacitance for most applications. If larger amounts of capacitance are desired for improved line support and transient response, tantalum capacitors can be used. Aluminum electrolytic with ultra low ESR such as Sanyo Oscon can be used, but are usually prohibitively expensive. Typical AI electrolytic capacitors are not suitable for switching frequencies above 500 kHz due to significant ringing and temperature rise due to self-heating from ripple current. An output capacitor with excessive ESR can also reduce phase margin and cause instability. In general, if electrolytic are used, it is recommended that. They be paralleled with ceramic capacitors to reduce ringing, switching losses, and output voltage ripple.

## Selecting The Input Capacitor

An input capacitor is required to serve as an energy reservoir for the current which must flow into the coil each time the switch turns ON. This capacitor must have extremely low ESR, so ceramic is the best choice. We recommend a nominal value of $4.7 \mu \mathrm{~F}$, but larger values can be used. Since this capacitor reduces the amount of voltage ripple seen at the input pin, it also reduces the amount of EMI passed back along that line to other circuitry.

### 1.6 MHz Boost Converter With 30V Internal FET Switch

## Application Hints

## Feed-Forward Compensation

Although internally compensated, the feed-forward capacitor Cf is required for stability. Adding this capacitor puts a zero in the loop response of the Converter. The recommended frequency for the zero fz should be approximately 6 kHz . Cf can be calculated using the formula:

$$
C f=1 /(2 \times \pi \times R 1 \times f z)
$$

## Selecting Diodes

The external diode used in the typical application should be a Schottky diode. A 20V diode such as the MBR0520 is recommended. The MBR05XX series of diodes are designed to handle a maximum average current of 0.5 A . For applications exceeding 0.5A average but less than 1A, a Microsemi UPS5817 can be used.

## Layout Hints

High frequency switching regulators require very careful layout of components in order to get stable operation and low noise. All components must be as close as possible to the AME5140 device. It is recommended that a 4-layer PCB be used so that internal ground planes are available. As an example, a recommended layout of components is shown:


Recommended PCB Component Layout (Top)

## Layout Hints



Recommended PCB Component Layout (Bottom)
Some additional guidelines to be observed:

1. Keep the path between L1, D1, and C2 extremely short. Parasitic trace inductance in series with D1 and C2 will increase noise and ringing.
2. The feedback components R1, R2 and CF must be kept close to the FB pin of U1 to prevent noise injection on the FB pin trace.
3. If internal ground planes are available use vias to connect directly to ground at pin 2 of U1, as well as the negative sides of capacitors C1 and C2.

## Duty Cycle

The maximum duty cycle of the switching regulator determines the maximum boost ratio of output-to-input voltage that the converter can attain in mode of operation. The duty cycle for a given boost application is defined as: This applies for continuous mode operation.

$$
D=\frac{v_{\text {OUT }}+V_{\text {DIODE }}-v_{I N}}{v_{\text {OUT }}+v_{\text {DIODE }}-v_{S W}}
$$

## AME5140

### 1.6 MHz Boost Converter with 30V Internal FET Switch

## ■ Application Hints

## Calculating Load Current

The load current is related to the average inductor current by the relation:

$$
\mathrm{I}_{\text {LOAD }}=\mathrm{I}_{\mathrm{IND}}(\mathrm{AVG}) \times(1-\mathrm{D})
$$

Where " $D$ " is the duty cycle of the application. The switch current can be found by:

$$
I_{S W}=I_{\text {IND }}(A V G)+1 / 2\left(I_{\text {RIPPLE }}\right)
$$

Inductor ripple current is dependent on inductance, duty cycle, input voltage and frequency:

$$
\mathrm{I}_{\text {RIPPLE }}=\mathrm{D} \times\left(\mathrm{V}_{\mathbb{I N}}-\mathrm{V}_{\mathrm{SW}}\right) /(\mathrm{f} \times \mathrm{L})
$$

Combining all terms, we can develop an expression which allows the maximum available load current to be calculated:

$$
I_{L O A D}=(1-D) \times\left(I_{S W}(\max )-\frac{D\left(V_{I N}-V_{S W}\right)}{2 f L}\right)
$$

## Thermal Consuderations

At higher duty cycles, the increased ON time of the FET means the maximum output current will be determined by power dissipation within the AME5140 FET switch. The switch power dissipation from ON-state conduction is calculated by:

$$
\mathrm{P}_{(\mathrm{SW})}=\mathrm{D} \times \mathrm{I}_{\mathrm{IND}(\mathrm{AVE}) 2} \times \mathrm{R}_{\mathrm{DS}}(\mathrm{ON})
$$

There will be some switching losses as well, so some derating needs to be applied when calculating IC power dissipation.

## Inductor Suppliers

Recommended suppliers of inductors for this product include, but are not limited to Sumida, Coilcraft, Panasonic, TDK and Murata. When selecting an inductor, make certain that the continuous current rating is high enough to avoid saturation at peak currents. A suitable core type must be used to minimize core (switching) losses, and wire power losses must be considered when selecting the current rating.

## Shutdown Pin Operation

The device is turned off by pulling the shutdown pin low. If this function is not going to be used, the pin should be tied directly to $\mathrm{V}_{\mathbb{I N}}$. If the SHDN function will be needed, a pull-up resistor must be used to $\mathrm{V}_{\text {IN }}$ (approximately 50k100k recommended). The EN pin must not be left unterminated.

### 1.6 MHz Boost Converter With 30V Internal FET Switch

Application Hints


Figure 5: 3S10P White LEDs Application in Li-Ion Battery



### 1.6 MHz Boost Converter with 30V Internal FET Switch

Application Hints


Figure 6: 6S3P White LEDs Application in Li-lon Battery


Efficiency Vs $\mathrm{I}_{\text {out }}$


### 1.6 MHz Boost Converter With 30V Internal FET Switch

Application Hints


Figure 7: 6S4P White LEDs Application in Li-Ion Battery


### 1.6 MHz Boost Converter with 30V Internal FET Switch

## Application Hints



Figure 8: 6S5P White LEDs Application in Li-Ion Battery




### 1.6 MHz Boost Converter With 30V Internal FET Switch



Oscillator Frequency vs Temperature


Feedback Bias Current vs Temperature

$I_{Q} V_{\text {IN }}$ (Idle) vs Temperature


Max. Duty Cycle vs Temperature


Efficiency vs Load Current


### 1.6 MHz Boost Converter with 30V Internal FET Switch



Efficiency vs Load Current


Efficiency vs Load Current



Efficiency vs Load Current


### 1.6 MHz Boost Converter With 30V Internal FET Switch






Output Voltage vs Load Current


Feedback Voltage vs Temperature


AME5140

### 1.6 MHz Boost Converter with 30V Internal FET Switch



■ Date Code Rule

| Marking |  |  | Date Code |  | Year |
| :---: | :---: | :---: | :---: | :---: | :---: |
| A | A | A | W | W | xxx0 |
| A | A | A | W | W | xxx1 |
| A | A | A | W | W | xxx2 |
| A | A | A | W | W | xxx3 |
| A | A | A | W | W | xxx4 |
| A | A | A | W | W | xxx5 |
| A | A | A | W | W | xxx6 |
| A | A | A | W | W | xxx7 |
| A | A | A | W | W | xxx8 |
| A | A | A | W | W | xxx9 |

## ■ Tape and Reel Dimension

SOT-25


Carrier Tape, Number of Components Per Reel and Reel Size

| Package | Carrier Width (W) | Pitch (P) | Part Per Full Reel | Reel Size |
| :---: | :---: | :---: | :---: | :---: |
| SOT- 25 | $8.0 \pm 0.1 \mathrm{~mm}$ | $4.0 \pm 0.1 \mathrm{~mm}$ | 3000 pcs | $180 \pm 1 \mathrm{~mm}$ |

### 1.6 MHz Boost Converter with 30V Internal FET Switch

## ■ Tape and Reel Dimension

TSOT-25


Carrier Tape, Number of Components Per Reel and Reel Size

| Package | Carrier Width (W) | Pitch (P) | Part Per Full Reel | Reel Size |
| :---: | :---: | :---: | :---: | :---: |
| TSOT-25 | $8.0 \pm 0.1 \mathrm{~mm}$ | $4.0 \pm 0.1 \mathrm{~mm}$ | 3000 pcs | $180 \pm 1 \mathrm{~mm}$ |

DFN-8
(3mmx3mmx0.75mm)


Carrier Tape, Number of Components Per Reel and Reel Size

| Package | Carrier Width (W) | Pitch (P) | Part Per Full Reel | Reel Size |
| :---: | :---: | :---: | :---: | :---: |
| DFN-8 <br> $(3 \times 3 \times 0.75 \mathrm{~mm})$ | $12.0 \pm 0.1 \mathrm{~mm}$ | $4.0 \pm 0.1 \mathrm{~mm}$ | 3000 pcs | $330 \pm 1 \mathrm{~mm}$ |

# 1.6 MHz Boost Converter With 30V Internal FET Switch 

Tape and Reel Dimension


Carrier Tape, Number of Components Per Reel and Reel Size

| Package | Carrier Width (W) | Pitch (P) | Part Per Full Reel | Reel Size |
| :---: | :---: | :---: | :---: | :---: |
| MSOP-8 | $12.0 \pm 0.1 \mathrm{~mm}$ | $4.0 \pm 0.1 \mathrm{~mm}$ | 4000 pcs | $330 \pm 1 \mathrm{~mm}$ |

### 1.6 MHz Boost Converter with 30V Internal FET Switch

## AME5140

## Package Dimension

SOT-25


Front View


TSOT-25


Front View


Side View


| SYMBOLS | MILLIMETERS |  | INCHES |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |  |  |
| $\mathbf{A + A}_{\mathbf{1}}$ | 0.90 | 1.25 | 0.0354 | 0.0492 |  |  |
| b | 0.30 | 0.50 | 0.0118 | 0.0197 |  |  |
| c | 0.09 | 0.25 | 0.0035 | 0.0098 |  |  |
| D | 2.70 | 3.10 | 0.1063 | 0.1220 |  |  |
| E | 1.40 | 1.80 | 0.0551 | 0.0709 |  |  |
| $\mathbf{e}$ | 1.90 BSC |  | 0.07480 BSC |  |  |  |
| $\mathbf{H}$ | 2.40 | 3.00 | 0.09449 | 0.11811 |  |  |
| $\mathbf{L}$ | 0.35 BSC |  | 0.0138 BSC |  |  |  |
| $\theta \mathbf{1}$ | $0^{\circ}$ |  | $10^{\circ}$ | $0^{\circ}$ |  | $10^{\circ}$ |
| $\mathbf{S}_{1}$ | 0.95 BSC |  | 0.0374 BSC |  |  |  |

### 1.6 MHz Boost Converter With 30V Internal FET Switch

Package Dimension

## DFN-8 (3mmx3mmx0.75mm)



TOP VIEW


REAR VIEW


| SYMBOLS | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
| A | 0.700 | 0.800 | 0.028 | 0.031 |
| D | 2.900 | 3.100 | 0.114 | 0.122 |
| E | 2.900 | 3.100 | 0.114 | 0.122 |
| e | 0.600 | 0.700 | 0.024 | 0.028 |
| D1 | 2.200 | 2.400 | 0.087 | 0.094 |
| E1 | 1.400 | 1.600 | 0.055 | 0.063 |
| b | 0.200 | 0.320 | 0.008 | 0.013 |
| L | 0.375 | 0.575 | 0.015 | 0.023 |
| G | 0.153 | 0.253 | 0.0060 | 0.010 |
| G1 | 0.000 | 0.050 | 0.0000 | 0.002 |

## AME5140

### 1.6 MHz Boost Converter with 30V Internal FET Switch

## ■ Package Dimension

DETAIL A


| SYMBOLS | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
| A | - | 1.07 | - | 0.04197 |
| $\mathrm{A}_{1}$ | 0.05 | 0.20 | 0.002 | 0.008 |
| A2 | 0.81 | 0.92 | 0.032 | 0.036 |
| b | 0.28 | 0.38 | 0.011 | 0.015 |
| b1 | 0.28 | 0.33 | 0.011 | 0.013 |
| c | 0.13 | 0.23 | 0.005 | 0.009 |
| c1 | 0.13 | 0.17 | 0.005 | 0.006 |
| D | 2.90 | 3.10 | 0.114 | 0.122 |
| E | 4.77 | 4.98 | 0.188 | 0.196 |
| E1 | 2.90 | 3.10 | 0.114 | 0.122 |
| e | 0.65 TYP |  | 0.0255 TYP |  |
| e1 | 1.95 TYP |  | 0.0767 TYP |  |
| L | 0.406 | 0.686 | 0.01598 | 0.02701 |
| L1 | 0.94 REF |  | 0.037 REF |  |
| L2 | 0.254 TYP |  | 0.010 TYP |  |
| $\theta$ | $0^{\circ}$ | $8^{\circ}$ | $0^{\circ}$ | $8^{\circ}$ |



## Life Support Policy:

These products of AME, Inc. are not authorized for use as critical components in life-support devices or systems, without the express written approval of the president of AME, Inc.
AME, Inc. reserves the right to make changes in the circuitry and specifications of its devices and advises its customers to obtain the latest version of relevant information.
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[^0]:    Note: ww represents the date code and pls refer to Date Code Rule before Package Dimension.

    * A line on top of the first letter represents lead free plating such as BDRww.

    Please consult AME sales office or authorized Rep./Distributor for the availability of package type.

[^1]:    * Measure $\theta_{\mathrm{JC}}$ on backside center of molding compund if IC has no tab.
    ** MIL-STD-202G 210F

